SILICON (Si) POWER MOSFET A CEZ12R10



CEZ12R10

100V ▲ 9.5mΩ ▲ 55A ▲ Si MOSFET

SILICON SI MOSFET A SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy PPAK5x6 package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability

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MAXIMUM RATINGS

Parameter (T _A = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	100V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at R _{TH_JC}	Ι _D	55A
Continuous Drain Current at R _{TH_JA}	Ι _D	16A
Pulsed Drain Current Note 1	I _{DM}	220A
Pulsed Drain Current Note 1	I _{DM}	64A
Maximum Power Dissipation	P _D	69W
Single Pulsed Avalanche Energy Note 5	E _{AS}	84.5mJ
Single Pulsed Avalanche Current Note 5	I _{AS}	13A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	1.8°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	20°C/W

APPLICATIONS

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+ 4 -	50			

PIN DESCRIPTION

Circuit Diagram	Outline - Bottom View	Pin No.	Description
D (5)	للصصطيا		
·		1	Source
G (4)		2	Source
		3	Source
		4	Gate
	لو_و_وا	5	Drain
S (1,2,3)	$\overline{4}$ $\overline{3}$ $\overline{2}$ $\overline{1}$		

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ELECTRICAL CHARACTERISTICS A T_A = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	100			V
Zero Gate Voltage Drain Current	V_{DS} = 100V, V_{GS} = 0V	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	$V_{GS(th)}$	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 20A$	R _{DS(ON)}		9.5	12	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	V_{DS} = 30V, V_{GS} = 0V, f = 1MHz	C _{ISS}		1135		рF
Output Capacitance	V_{DS} = 30V, V_{GS} = 0V, f = 1MHz	Coss		700		рF
Reverse Transfer Capacitance	V_{DS} = 30V, V_{GS} = 0V, f = 1MHz	C _{RSS}		5		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G}(\text{ext})}$ = 6 Ω	t _{D(ON)}		23		ns
Turn-On Rise Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 1A, $R_{G(\text{ext})}$ = 6 Ω	t _R		6		ns
Turn-Off Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 6 Ω	t _{D(OFF)}		43		ns
Turn-Off Fall Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 6 Ω	t _F		39		ns
Total Gate Charge	$V_{DS} = 50V, V_{GS} = 10V, I_D = 20A$	Q _G		19		nC
Gate Source Charge	$V_{DS} = 50V, V_{GS} = 10V, I_D = 20A$	Q _{GS}		4		nC
Gate Drain Charge	V_{DS} = 50V, V_{GS} = 10V, I_D = 20A	\mathbf{Q}_{GD}		7		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current ^{Note3}		۱ _s			55	А
Drain-Source Diode Forward Voltage ^{Note3}	V _{GS} = 0V, I _S = 20A	V_{SD}			1.2	V

Notes

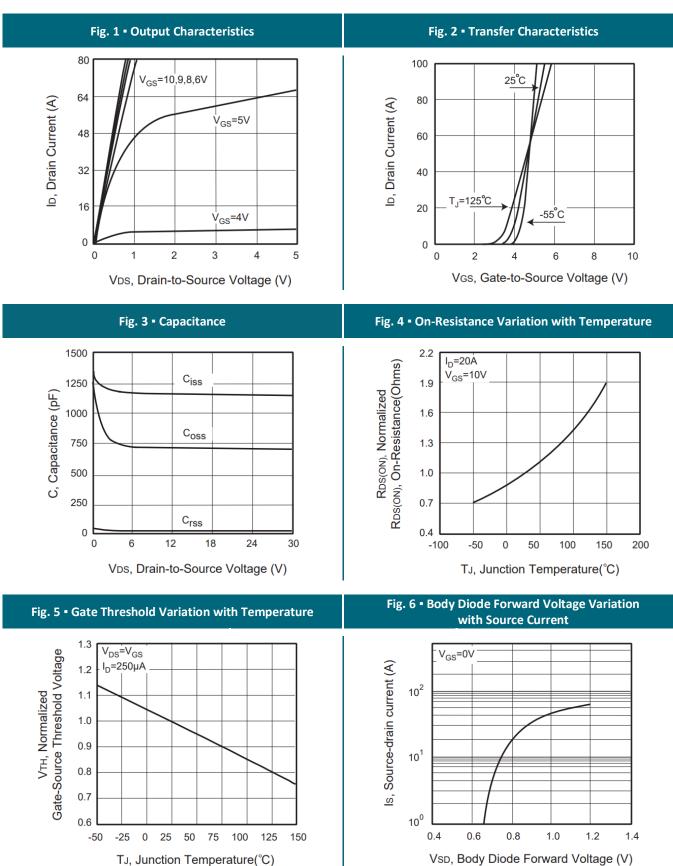
- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, $t \le 10$ sec
- 3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4: Guaranteed by design, not subject to production testing.
- 5: L = 1mH, $I_{AS} = 13A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$



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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

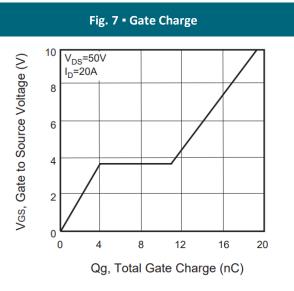
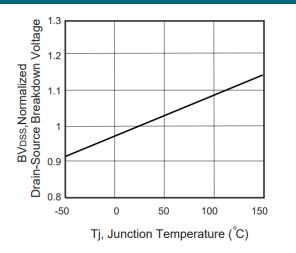


Fig. 9 - Breakdown Voltage Variation vs. Temperature



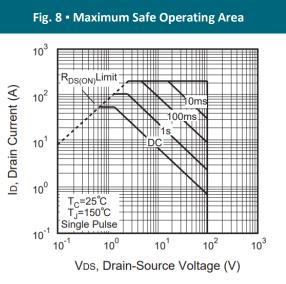


Fig. 10 • Switching Test Circuit

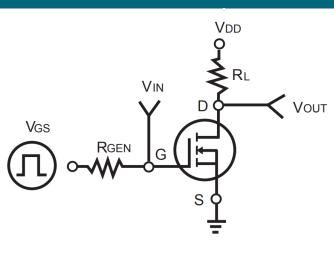
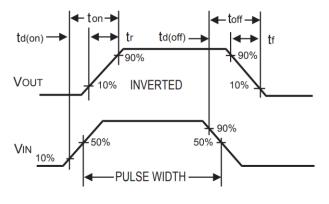


Fig. 11 • Switching Waveforms



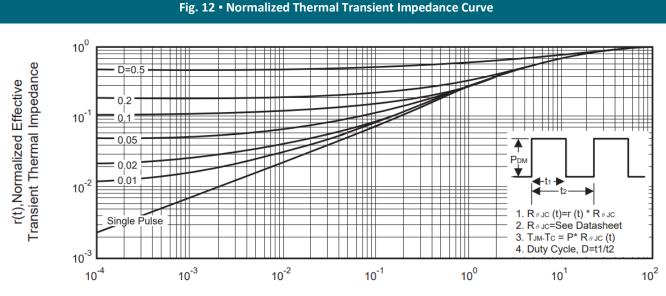
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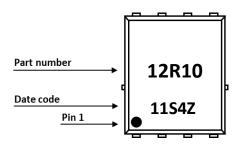
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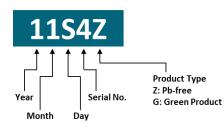
Square Wave Pulse Duration (sec)

PART MARKING



DATE CODE

Example: 11S4Z



Coding list for "Day"										
1	2	3	4	5	6	7	8	9	А	
01	02	03	04	05	06	07	08	09	10	
В	С	D	Ε	F	G	Н		J	K	
11	12	13	14	15	16	17	18	19	20	
L	Μ	Ν	0	Ρ	Q	R	S	Т	U	
21	22	23	24	25	26	27	28	29	30	
V										
31										

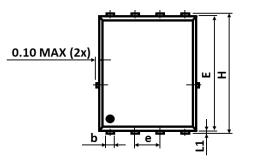
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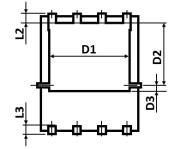


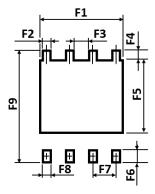


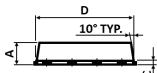
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PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	0.800	-	1.170	E	5.650	-	5.900
b	0.340	-	0.490	е		1.270 TYP	
с	0.200	-	0.340	Н	5.900	-	6.150
D	4.800	-	5.100	L1	0.050	-	0.250
D1	3.800	-	4.200	L2	0.380	-	0.620
D2	3.180	-	3.780	L3	0.380	-	0.750
D3	0.150	-	0.360				

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	4.500	-	F6	-	0.800	-
F2	-	0.500	-	F7	-	1.270	-
F3	-	0.770	-	F8	-	0.500	-
F4	-	0.550	-	F9	-	6.250	-
F5	_	3.650	_				

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEZ12R10	PPAK 5x6	Reel	2,500pcs	5,000pcs	40,000pcs	

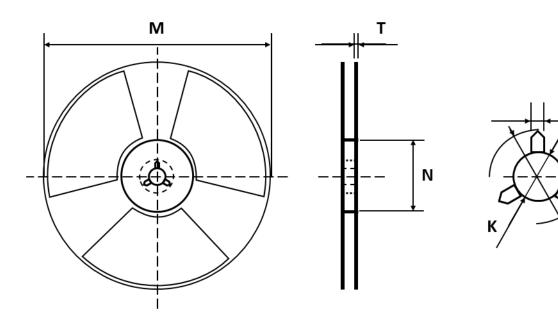


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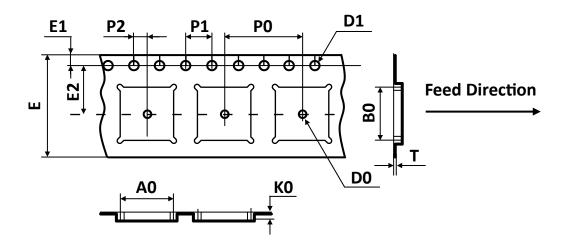


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
12mm	Ø330	±2.00	±1.00	±0.20	±0.50	+0.50 -0.20	±0.50

TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
	6.50	5.28	2.00	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
PPAK 5x6	±0.10	±0.10	±0.10	±0.25	±0.10	+0.30 -0.10	±0.10	±0.05	±0.10	±0.10	±0.05	±0.02



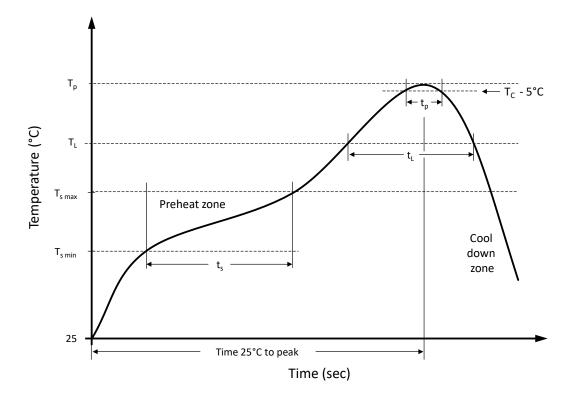
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RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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